

In the Title

✓ On page 1, the Title has been amended as shown below:

~~Integrated Circuitry~~ MOS Transistors With Nitrogen in the Gate Oxide of the P-Channel Transistor

In the Specification:

At page 1, the paragraph inserted before the "Technical Field" by the amendment dated February 27, 2002, has been replaced with the paragraph shown below:

RELATED PATENT DATA

This application resulted from a continuation application of U.S. Patent Application Serial No. 09/444,024, filed November 19, 1999, entitled "P-Type FET in a CMOS With Nitrogen Atoms in the Gate Dielectric", naming Jigish D. Trivedi, Zhongze Wang and Rhongsheng Yang as inventors, now U.S. Patent No. 6,417,546 B2, which was a divisional application of Patent Application Serial No. 09/386,076, filed August 30, 1999, now Patent No. 6,093,661, issued July 25, 2000, entitled "Integrated Circuitry and Semiconductor Processing Method of Forming Field Effect Transistors", naming Jigish D. Trivedi, Zhongze Wang and Rongsheng Yang as inventors, the disclosure of which is incorporated by reference.